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## Low-firing and temperature stable microwave dielectric ceramics:

### $\text{Ba}_2\text{LnV}_3\text{O}_{11}$ (Ln = Nd, Sm)

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#### Abstract

Low-firing and temperature stable microwave dielectric ceramics of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) were prepared by solid-state reaction. X-ray diffraction (XRD) and scanning electron microscopy (SEM) were used to investigate the phase purity, crystal structure, sintering behavior, and microstructure. The XRD patterns indicated that  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics belong to monoclinic crystal system with  $P2_1/c$  space group in the whole sintering temperature range (800-900 °C). Both ceramics could be well densified at 880 °C for 4 h with relative densities higher than 96%. The  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) samples

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sintered at 880 °C for 4 h exhibited excellent microwave dielectric properties:  $\varepsilon_r = 12.05$ ,  $Q \times f = 23,010$  GHz,  $\tau_f = -7.7$  ppm/°C, and  $\varepsilon_r = 12.19$ ,  $Q \times f = 27,120$  GHz,  $\tau_f = -16.2$  ppm/°C, respectively. Besides,  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) ceramics could be well co-fired with the silver electrode at 880 °C.

**Keywords:**  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm); Microwave dielectric properties; LTCC; Chemical compatibility.

## 1. Introduction

Microwave dielectric devices have been widely used in dielectric resonators, dielectric filters, and dielectric antennas, etc.<sup>1, 2</sup> In the last few decades, the rapid development in wireless communications, such as satellite broadcasting, radar transponder, 5G wireless systems, and Internet of Things (IoT), has led to extensive studies on the microwave dielectric ceramics with high performance.<sup>3-6</sup> For practical applications, an appropriate relative permittivity ( $\varepsilon_r$ ), a near-zero temperature coefficient of resonant frequency ( $\tau_f$ ) for thermal stability, and a high quality factor ( $Q \times f$ ) for frequency selectivity are crucially required.<sup>7-10</sup> In addition, in order to fulfill the rapidly increasing demand for miniaturization and integration, low temperature co-fired ceramic (LTCC) technology has gained substantial attention and vast development. LTCC technology has become a crucial step in the fabrication of integrated circuits. For LTCC applications, the microwave dielectric materials are primarily required to have low sintering temperatures to co-fire with the commonly used and highly conducting metals (e.g. 960 °C for Ag and 1083 °C for Cu).<sup>11-14</sup>

Recently, a large number of glass-free low temperature firing microwave dielectric materials have been reported. Most of them are based on the material systems with low-melting-points constituents, for example,  $\text{BiVO}_4$ ,<sup>15</sup>  $\text{BaCaV}_2\text{O}_7$ ,<sup>16</sup>  $\text{Ca}_5\text{Ni}_4(\text{VO}_4)_6$ ,<sup>17</sup>  $\text{Mg}_2\text{SiO}_4$ .<sup>18</sup> In recent decades, good microwave dielectric properties have also been reported in some Ln-based vanadate ceramics.<sup>19-21</sup> For example, the  $\text{NdVO}_4$  ceramic sintered at 1160 °C for 4 h possessed excellent microwave dielectric properties:  $\varepsilon_r = 12.0$ ,  $Q \times f = 36,440$  GHz, and  $\tau_f = -44.3$  ppm/°C.<sup>20</sup> In our previous work, the microwave dielectric properties of compounds in the ternary vanadates  $\text{BaO-Ln}_2\text{O}_3\text{-V}_2\text{O}_5$  were characterized. Among them,  $\text{Ba}_2\text{LaV}_3\text{O}_{11}$  has attracted extensive attention in recent years due to its excellent microwave dielectric properties ( $\varepsilon_r = 12.8$ ,  $Q \times f = 31,800$  GHz, and  $\tau_f = -14.0$  ppm/°C), and low sintering temperature (840 °C).<sup>22</sup> We also found that  $\text{Ba}_2\text{BiV}_3\text{O}_{11}$  ceramic could be densified at 870 °C and possessed good microwave dielectric properties with  $\varepsilon_r = 14.2$ ,  $Q \times f = 68,700$  GHz, and  $\tau_f = -81.0$  ppm/°C.<sup>23</sup> This stimulates us to investigate whether other compounds in  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  system exhibit good microwave dielectric properties. Therefore, in this work,  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics were prepared with an attempt to develop novel low-firing ceramics. The microstructures and microwave dielectric properties were investigated. Their chemical compatibility with silver (Ag) has also been investigated.

## 2. Experimental section

### 2.1. Preparation

$\text{Ba}_2\text{LnV}_3\text{O}_{11}$  ceramics were prepared by the conventional solid state method with high-purity  $\text{BaCO}_3$ ,  $\text{Nd}_2\text{O}_3$ ,  $\text{Sm}_2\text{O}_3$ , and  $\text{NH}_4\text{VO}_3$  (> 99%, Guo-Yao Co., Ltd., Shanghai, China) as starting reagents. The stoichiometrically weighed powders were mixed and ball-milled in alcohol medium for 6 h, followed by drying at 120 °C. The dried powders were calcined at 750 °C for 4 h, and then re-milled for 6 h. The resultant powders were granulated with polyvinyl alcohol (PVA, 10 vol%) as a binder, and pressed into cylindrical pellets of 10 mm in diameter and 6 mm in thickness in a steel die under a pressure of 350 MPa. The pellets were first heated at 550 °C in air for 4 h at a heating rate of 1.5 °C/min to burn out the organic binder, and then sintered over a temperature range of 800 °C–900 °C for 4 h with a heating rate of 5 °C/min.

### 2.2 Characterizations

The powder X-ray diffraction (XRD) ( $\text{CuK}\alpha 1$ , 1.54059 Å, Model X'Pert PRO, PANalytical, Almelo, Holland) was carried out on the calcined powders to identify the crystal structure and phase purity. The microstructures of the ceramics were characterized by field emission scanning electron microscopy (FE-SEM, Model S4800, Hitachi, Japan). The densities of the sintered ceramics were determined using the Archimedes' method. The dielectric properties at microwave frequencies were recorded by the network analyzer (Model N5230A, Agilent Co., Palo Alto, California) and temperature chamber (Delta 9039, Delta Design, San Diego, CA). The temperature coefficient of resonant frequency ( $\tau_f$ ) was

calculated by the equation:

$$\tau_f = \frac{f_{T_1} - f_{T_0}}{f_{T_0}(T_1 - T_0)} \quad (1)$$

where,  $f_{T_1}$  and  $f_{T_0}$  were the resonant frequencies at 85 °C and room temperature, respectively.

### 3. Results and discussion

#### 3.1 Structure and morphology

Fig. 1(a) depicts the XRD patterns of the calcined  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  powders at 750 °C for 4 h. Both compounds exhibited similar diffraction patterns and all the observed peaks matched well with the standard card JCPDS No. 40-0105 for  $\text{Ba}_2\text{LaV}_3\text{O}_{11}$ .

This result indicates that  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  well crystallized in single phase with a monoclinic space group  $P2_1/c$  (14). The lattice parameters were calculated by the least square refinement with  $a = 12.37 \text{ \AA}$ ,  $b = 7.76 \text{ \AA}$ ,  $c = 11.26 \text{ \AA}$ ,  $\beta = 103.5^\circ$ , and  $V = 1051.82 \text{ \AA}^3$  for  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $a = 12.35 \text{ \AA}$ ,  $b = 7.74 \text{ \AA}$ ,  $c = 11.23 \text{ \AA}$ ,  $\beta = 103.2^\circ$ , and  $V = 1047.12 \text{ \AA}^3$  for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$ , respectively. The schematic of crystal structure for  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  is shown in Fig. 1(b). As shown, Ln atoms are six-coordinated in distorted octahedra and  $[\text{LnO}_6]$  octahedra are edge-sharing, while V atoms are connected with four neighboring oxygen forming  $[\text{VO}_4]$  tetrahedra. The adjacent  $[\text{LnO}_6]$  octahedra and  $[\text{VO}_4]$  tetrahedra are corner shared. Ba atoms are located in the interspace of the tetrahedra and octahedra.

Fig. 2(a-e) shows SEM micrographs of  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  ceramics sintered at 820 °C to 900 °C and Fig. 2(f) for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  sintered at 880 °C. As shown, a porous microstructure with an average grain size of 1–2  $\mu\text{m}$  was observed in the  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  samples sintered at 820 °C. With the increasing sintering temperature, the amount of pore decreased and the grains

gradually grew up. As the sintering temperature increased to 880 °C, a homogeneous microstructure with evidently identifiable grain boundaries was obtained for Ba<sub>2</sub>NdV<sub>3</sub>O<sub>11</sub>. However, further increase in sintering temperature to 900 °C induced abnormal grain growth with large grains (~ 6 μm). Similar phenomena were observed in Ba<sub>2</sub>SmV<sub>3</sub>O<sub>11</sub> ceramics, and the ceramic sintered at 880 °C exhibited dense microstructure with closely-packed grains, as shown in Fig. 2(f).

### 3.2 Microwave dielectric properties

The variations in the relative density and relative permittivity of the Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> ceramics as a function of sintering temperature are shown in Fig. 3. With increasing sintering temperature, the relative density gradually increased to a maximum value and then declined slightly. The optimum densification temperatures for both ceramics were determined to be 880 °C with a maximum relative density of 96.2 % for Ba<sub>2</sub>NdV<sub>3</sub>O<sub>11</sub> and 97.1 % for Ba<sub>2</sub>SmV<sub>3</sub>O<sub>11</sub> ceramic, respectively.

As shown in Fig. 3(b), the relative permittivity ( $\epsilon_r$ ) exhibited a similar variation trend with the increasing sintering temperature to the density and the saturated  $\epsilon_r$  values were achieved in the best sintered samples with  $\epsilon_r = 12.05$  for Ba<sub>2</sub>NdV<sub>3</sub>O<sub>11</sub> and 12.19 for Ba<sub>2</sub>SmV<sub>3</sub>O<sub>11</sub>, respectively. This result suggests the crucial effect of density on the relative permittivity, especially for the samples with porosity. Thus, to eliminate the effects of porosity, the relative permittivity was corrected according to by the Bosman and Having's porosity correction equation:<sup>24, 25</sup>

$$\epsilon_{corr} = \epsilon_r(1 + 1.5p) \quad (2)$$

where,  $p$  is the fractional porosity. The  $\varepsilon_{corr}$  values of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics at 880 °C are about 12.73 and 12.74, respectively. Besides, the theoretical permittivity was evaluated according to Clausius–Mossotti equation:<sup>26, 27</sup>

$$\varepsilon_r = \frac{1 + 2b\alpha_D^T/V_m}{1 - b\alpha_D^T/V_m} \quad (3)$$

where,  $b = 4\pi/3$ ,  $\alpha_D^T$  is the molecular polarizability and  $V_m$  is the cell volume. The calculated theoretical permittivity of  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  is 12.14 and 12.09 for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$ . The slightly higher theoretical permittivity of  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  than its Sm counterpart could be due to the larger ionic polarizability of  $\text{Nd}^{3+}$  (5.01 Å) than  $\text{Sm}^{3+}$  (4.74 Å). Additionally, the relative error between the porosity corrected  $\varepsilon_r$  and the theoretical density is about 7.2% for the  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  ceramic and 8.3% for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  ceramic, which indicates that ionic polarization plays a prominent role in the dielectric polarizability in the microwave frequency region.<sup>11, 28</sup>

Fig. 4 shows the  $Q \times f$  and  $\tau_f$  values of the  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  ceramics sintered at different temperatures for 4 h. Similar to the density and relative permittivity, the quality factors also exhibited strong dependency on the sintering temperature. With increasing sintering temperature, the  $Q \times f$  values initially increased to a maximum value and then decreased. The maximum  $Q \times f$  values of 23,010 GHz for  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and 27,120 GHz for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  were obtained at 880 °C for 4 h, respectively. In general, the  $Q \times f$  value depends on the intrinsic parameters such as structural characteristics and the extrinsic parameters such as porosity, secondary phases, and lattice defects.<sup>29, 30</sup> For ceramics with high relative densities > 95 % and no secondary phases, the extrinsic impacts on  $Q \times f$  value could be depressed. According to the study of Kim *et al.*,<sup>31</sup> the  $Q \times f$  also could be highly

dependent on the packing fraction. The packing fraction could be calculated by the equation:

$$\text{packing fraction (\%)} = \frac{\text{volume of packed ions}}{\text{volume of unit cell}} \times Z \quad (4)$$

where,  $Z$  is the number of formula units per unit cell. The packing fraction of  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  is 57.9 %, and 58.1 % for  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$ . For comparison, the calculated packing fractions for  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  ( $\text{Ln} = \text{Bi}, \text{La}, \text{Nd}, \text{Sm}$ ) ceramics are listed in Table 1.  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  ceramics with lower Ln-site ionic radius decreased the unit cell volume, which in turn increased the packing fraction. It is obviously seen that a larger packing fraction directly corresponds to a higher  $Q \times f$  value. Therefore, the variation in the  $Q \times f$  value of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  ( $\text{Ln} = \text{Bi}, \text{La}, \text{Nd}, \text{Sm}$ ) ceramics could be explained by the difference in packing fraction.<sup>32</sup> The increase in packing fraction indicates that the space for lattice vibrations decreases, and thus reduces the intrinsic loss.

As presented in Fig. 4(b), over the sintering temperature range from 800-900 °C, no significant change in the  $\tau_f$  value was observed. When sintered at 880 °C for 4 h,  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  possessed a near-zero  $\tau_f$  value of  $-7.7 \text{ ppm}/^\circ\text{C}$  while  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  had a relatively negative  $\tau_f$  value of  $-16.2 \text{ ppm}/^\circ\text{C}$ . The  $\tau_f$  value is a function of the temperature coefficient of the dielectric constant ( $\tau_\epsilon$ ) and the linear thermal expansion coefficient ( $\alpha_L$ ), as show in equation:<sup>33</sup>

$$\tau_f = -\left(\frac{\tau_\epsilon}{2} + \alpha_L\right) \quad (5)$$

where,  $\alpha_L$  is a typically constant for dielectric ceramics, and  $\tau_\epsilon$  depends on the tilting of oxygen octahedral.<sup>34</sup> The degree of tilting on oxygen octahedral could be reflected by the bond valence and bond length between the cations and oxygen atoms. According to the bond



valence theory, the  $\tau_f$  value is related to chemical nature of ions, the distance between cations and anions, the bond valence of oxygen octahedra.<sup>35, 36</sup>

According to Fig. 1(b), Ln atoms are six-coordinated in octahedra. The bond valences between Ln cations and oxygen ions of the  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  ceramics calculated by the following formulas:

$$V_i = \sum_j v_{ij} \quad (6)$$

$$v_{ij} = \exp\left[\frac{R_{ij} - d_{ij}}{b}\right] \quad (7)$$

where  $R_{ij}$  is the bond valence parameter,  $d_{ij}$  is the length of a bond between atoms i and j, and  $b$  is a universal constant (0.37 Å).<sup>37</sup> As shown in Table 1,  $V_{\text{Ln}}$  is 3.082 and 3.305 for  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$ . The increase in bond valence of Ln cation results in an increase in bond strength between Ln cation with oxygen, which in turn increases the thermal energy for tilted structure recovering, and thus  $\tau_f$  value decreased.<sup>38</sup>

### 3.3 Chemical compatibility with silver electrode

For LTCC applications, the microwave dielectric materials should have chemical compatibility with metal electrodes. Silver is a commonly used electrode material because of its high electric conductivity and relatively low price. In the present work, 15 wt% Ag powder was mixed with the  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) and co-fired at 880 °C for 4 h to confirm their chemical compatibility. XRD patterns and SEM images of the co-fired ceramics are shown in Fig. 5. Only the diffraction peaks of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) and silver (marked with “Ag” in Fig.5) were detected in the XRD patterns. Additionally, SEM images showed two different kinds of grains with the larger grains to be Ag. Thus, no chemical reaction occurred between the  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics and Ag electrode when

sintered at 880 °C for 4 h. All the results indicate that Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) ceramics could be possible candidates for applications in LTCC technology due to their low sintering temperature, excellent microwave dielectric properties, and reliable compatibility with silver electrodes.

Table 2 displays the sintering temperatures, microwave dielectric properties and chemical compatibility with Ag electrode of some LTCC materials. All these ceramics possess low sintering temperatures (lower than 960 °C) except for NdVO<sub>4</sub>. The microwave permittivity of the Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) ceramics is comparable to the garnet structured Na<sub>2</sub>LnMg<sub>2</sub>V<sub>3</sub>O<sub>12</sub> (Ln = Nd, Sm), whereas the quality factor is inferior to BaMg<sub>2</sub>(VO<sub>4</sub>)<sub>2</sub>. However, Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) ceramics possess near-zero  $\tau_f$  values, which guarantees the thermal stability of materials and devices.

### 3.4 Thermal expansion

The variable-temperature (VT) XRD patterns performed on Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) over 25-120 °C are shown in Fig. 6. It is obvious that the main peaks of both ceramics slightly shifted with increasing measurement temperature, indicating the variation in the lattice parameters and cell volume. The unit cell parameters of Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) ceramics were refined using the least square method and shown in Fig. 7 as a function of temperature from 25 to 120 °C. As the temperature increased, the cell parameters *a*, *b*, *c*, and *V* slightly increased for both ceramics. This indicates Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Nd, Sm) ceramics have positive thermal expansion coefficient. From 25 to 120 °C, the thermal expansion coefficient coefficients of  $\alpha_a = 1.47 \times 10^{-6}$  and  $1.73 \times 10^{-6} \text{ K}^{-1}$ ,  $\alpha_b = 2.80 \times 10^{-6}$  and  $3.15 \times 10^{-6} \text{ K}^{-1}$ ,  $\alpha_c = 2.14 \times 10^{-6}$  and  $2.08 \times 10^{-6} \text{ K}^{-1}$ ,  $\alpha_V = 2.36 \times 10^{-6}$  and  $2.65 \times 10^{-6} \text{ K}^{-1}$  for Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> and Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub>, respectively.

## 4. Conclusions

This work has shown that low temperature sintering process could able to prepare the  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) single phase. The X-ray diffraction analyses indicated that  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) ceramics belong to monoclinic system with  $P2_1/c$  space group in the whole sintering temperature range.  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) ceramics could be well densified at temperature at 880 °C with relative densities higher than 96%. The  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) samples sintered at 880 °C for 4 h exhibited excellent microwave dielectric properties:  $\varepsilon_r = 12.05$  and  $12.19$ ,  $Q \times f = 23,010$  GHz and  $27,120$  GHz,  $\tau_f = -7.7$  ppm/°C and  $-16.2$  ppm/°C, respectively. Additionally,  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) ceramics could be co-fired with the silver electrode at 880 °C. All the results indicate that the  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln =Nd, Sm) ceramics are suitable materials in LTCC applications.

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**Table 1 The packing fraction, bond valence and microwave dielectric properties of Ba<sub>2</sub>LnV<sub>3</sub>O<sub>11</sub> (Ln = Bi, La, Nd, and Sm) ceramics**

Ceramics	S.T. (°C)	$\epsilon_r$	$Q \times f$ (GHz)	$\tau_f$ (ppm/°C)	Unit cell Volume(Å <sup>3</sup> )	Packing fraction (%)	V <sub>Ln-O</sub>	Reference
Ba <sub>2</sub> BiV <sub>3</sub> O <sub>11</sub>	870	14.20	68,700	−81	1049.40	59.5	3.081	[23]
Ba <sub>2</sub> LaV <sub>3</sub> O <sub>11</sub>	840	12.80	31,800	−14	1066.80	58.5	3.481	[22]
Ba <sub>2</sub> NdV <sub>3</sub> O <sub>11</sub>	880	12.05	23,010	−7.7	1051.82	57.9	3.082	This work
Ba <sub>2</sub> SmV <sub>3</sub> O <sub>11</sub>	880	12.19	27,120	−16.2	1047.12	58.1	3.305	This work

**Table 2 Sintering temperatures, microwave dielectric properties and chemical compatibility with Ag of some LTCC ceramics**

Ceramics	S.T. (°C)	$\epsilon_r$	$Q \times f$ (GHz)	$\tau_f$ (ppm/°C)	Reactivity with Ag	Reference
Ba <sub>2</sub> NdV <sub>3</sub> O <sub>11</sub>	880	12.05	23,010	-7.7	No	This work
Ba <sub>2</sub> SmV <sub>3</sub> O <sub>11</sub>	880	12.19	27,120	-16.2	No	This work
Ba <sub>2</sub> V <sub>2</sub> O <sub>7</sub>	900	10.1	51,630	-26.5	No report	[40]
BaCaV <sub>2</sub> O <sub>7</sub>	830	8.9	31,362	-68.2	No report	[16]
BaTa <sub>2</sub> V <sub>2</sub> O <sub>11</sub>	870	28.2	41,958	+90	Yes	[39]
BaMg <sub>2</sub> (VO <sub>4</sub> ) <sub>2</sub>	900	12	156,140	-36	No report	[41]
Ba <sub>16</sub> V <sub>18</sub> O <sub>61</sub>	620	9.7	80,100	-61	No	[42]
NdVO <sub>4</sub>	1160	12	36,440	-44.3	No report	[20]
Na <sub>2</sub> NdMg <sub>2</sub> V <sub>3</sub> O <sub>12</sub>	850	12	26,544	-63	No	[43]
Na <sub>2</sub> SmMg <sub>2</sub> V <sub>3</sub> O <sub>12</sub>	850	12.1	36,207	-69	No	[43]

## Figure Captions:

**Fig.1** The standard  $\text{Ba}_2\text{LaV}_3\text{O}_{11}$  (No. 40-0105) profile as well as the XRD patterns of the calcined  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  (a), and the schematic crystal structure of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) (b).

**Fig.2** SEM micrographs of  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  ceramics sintered at 820 °C to 900 °C (a-e) and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  sintered at 880 °C (f).

**Fig.3** Variation in relative density (a) and relative permittivity (b) of the  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  ceramics as a function of sintering temperature.

**Fig.4**  $Q \times f$  and  $\tau_f$  values of the  $\text{Ba}_2\text{NdV}_3\text{O}_{11}$  and  $\text{Ba}_2\text{SmV}_3\text{O}_{11}$  ceramics sintered at different temperatures for 4 h (the loss tangent shown in the inset).

**Fig.5** The XRD patterns and backscattered electron (BSE) images of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics with 15 wt% Ag cofired at 880 °C.

**Fig.6** Selected VT-XRD patterns of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) ceramics over 25-120 °C.

**Fig.7** The variation in unit cell parameters ( $a$ ,  $b$ ,  $c$ , and  $V$ ) of  $\text{Ba}_2\text{LnV}_3\text{O}_{11}$  (Ln = Nd, Sm) over 25-120 °C.











